

AMENDMENTS TO THE CLAIMS

In the Claims

1-19. (Cancelled)

20. (Previously Presented) A method of producing a crystalline substrate based device comprising:

providing a wafer including a semiconductor substrate and comprising a plurality of semiconductor microstructures including at least one optoelectronic device;

providing at least one wafer-level transparent packaging layer;

forming onto said at least one wafer-level transparent packaging layer, a wafer-level spacer, said packaging layer and said spacer defining a plurality of cavities extending entirely through said spacer;

sealing said wafer-level spacer to said semiconductor substrate, thereby fully defining a gap between ones of said plurality of microstructures and corresponding chip scale portions of said at least one transparent packaging layer, without requiring removal of material from said at least one transparent packaging layer overlying said at least one optoelectronic device; and

subsequently dicing said semiconductor substrate, having said wafer-level spacer and said at least one wafer-level transparent packaging layer sealed thereunto, to form individual chip scale packaged devices

21. (Cancelled)

22. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said sealing comprises using Epoxy to seal said wafer-level spacer onto said semiconductor substrate.

23. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said semiconductor substrate comprises silicon.

24. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said semiconductor substrate comprises lithium niobate.

25-26. (Cancelled)

27. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said plurality of semiconductor microstructures comprises at least one micromechanical structure.

28. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said plurality of semiconductor microstructures comprises at least one microelectronic structure.

29-32. (Cancelled)

33. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said semiconductor substrate comprises lithium tantalate.

34. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said plurality of semiconductor microstructures comprises at least one surface acoustic wave device.

35. (Cancelled)

36. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said semiconductor substrate comprises quartz.

37-38. (Cancelled)

39. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 wherein said plurality of semiconductor microstructures receives light via said at least one transparent packaging layer.

40. (Previously Presented) A method of producing a crystalline substrate based device according to claim 39 and wherein said sealing comprises using an adhesive to seal said wafer-level spacer onto said semiconductor substrate.

41. (Previously Presented) A method of producing a crystalline substrate based device according to claim 40 and wherein said adhesive comprises epoxy.

42. (Previously Presented) A method for producing a crystalline substrate based device according to claim 39 and wherein said semiconductor substrate comprises silicon.

43. (Cancelled)

44. (Previously Presented) A method of producing a crystalline substrate based device according to claim 39 and wherein said plurality of semiconductor microstructures comprises at least one micromechanical structure.

45. (Previously Presented) A method of producing a crystalline substrate based device according to claim 39 and wherein said plurality of semiconductor microstructures comprises at least one microelectronic structure.

46. (Cancelled)

47. (Previously Presented) A method for producing a crystalline substrate based device according to claim 39 and wherein said semiconductor substrate comprises lithium tantalate.

48. (Previously Presented) A method for producing a crystalline substrate based device according to claim 39 and wherein said plurality of semiconductor microstructures comprises at least one surface acoustic wave device.

49. (Previously Presented) A method for producing a crystalline substrate based device according to claim 39 and wherein said semiconductor substrate comprises quartz.

50. (Previously Presented) A method for producing a crystalline substrate based device according to claim 39 and wherein said semiconductor substrate comprises lithium niobate.

51-64. (Cancelled)

65. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 wherein the individual chip scale packaged devices have a multiplicity of electrical contacts plated along edge surfaces thereof.

66. (Cancelled)

67. (Cancelled)